

SANYO

No.4236

2SJ266

P-Channel MOS Silicon FET

Very High-Speed
Switching Applications**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Surface mount type device making the following possible.
 - Reduction in the number of manufacturing processes for 2SJ266-applied equipment.
 - High density surface mount applications.
 - Small size of 2SJ266-applied equipment.

Absolute Maximum Ratings at Ta = 25°C

			unit
Drain to Source Voltage	V_{DS}	-60	V
Gate to Source Voltage	V_{GS}	± 15	V
Drain Current(DC)	I_D	-8	A
Drain Current(Pulse)	I_{DP}	$PW \leq 10 \mu s, \text{ duty cycle} \leq 1\%$	-32 A
Allowable Power Dissipation	P_D	1.65	W
		$T_c = 25^\circ C$	50 W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

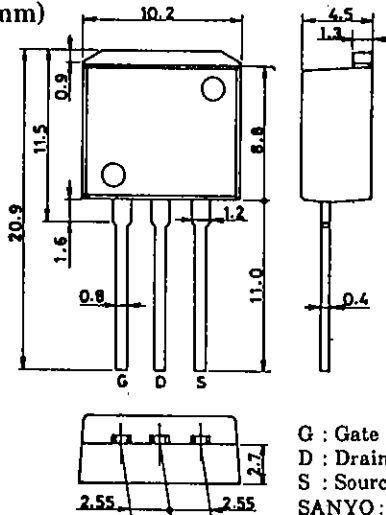
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-60			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100 \mu A, V_{DS} = 0$	± 15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0$			-100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -4A$	3.5	6		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -4A, V_{GS} = -10V$		0.15	0.2	Ω
		$I_D = -4A, V_{GS} = -4V$		0.2	0.27	Ω

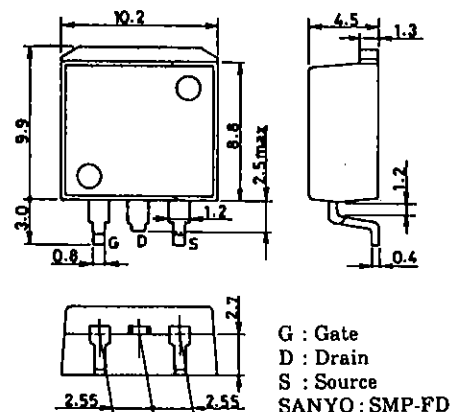
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Package Dimensions 2093

(unit : mm)

**Package Dimensions 2090**

(unit : mm)

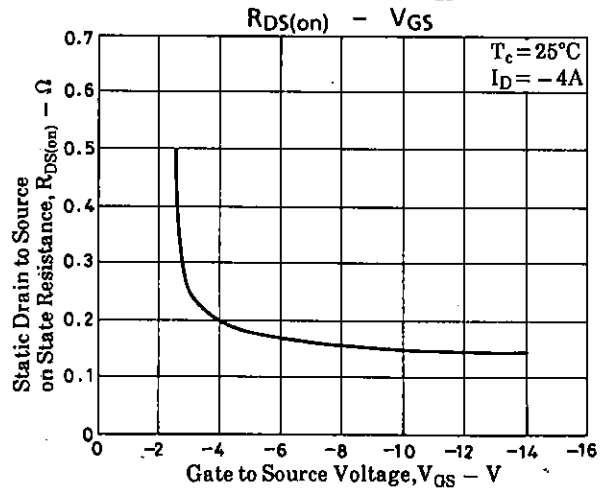
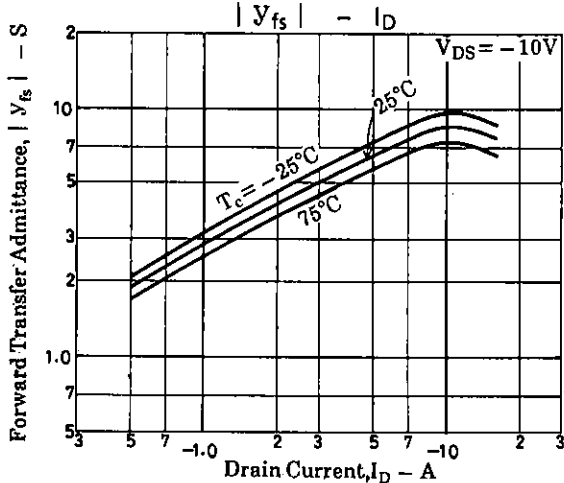
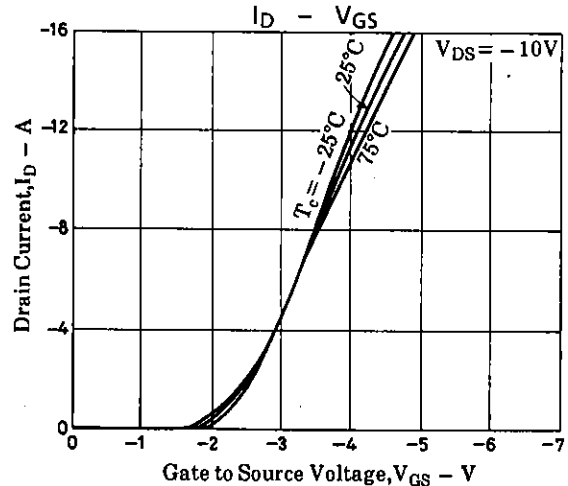
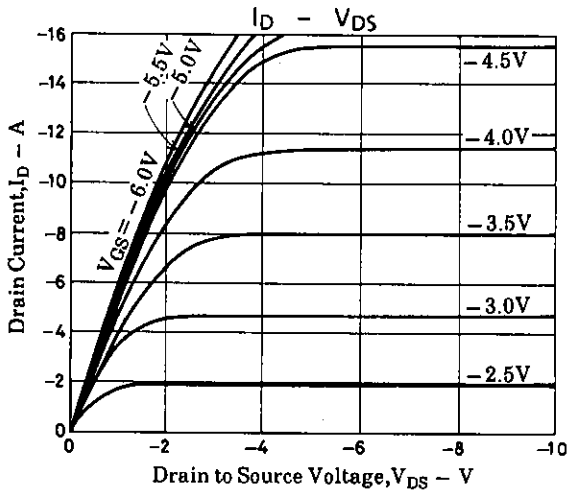
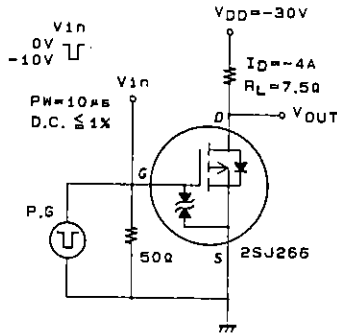
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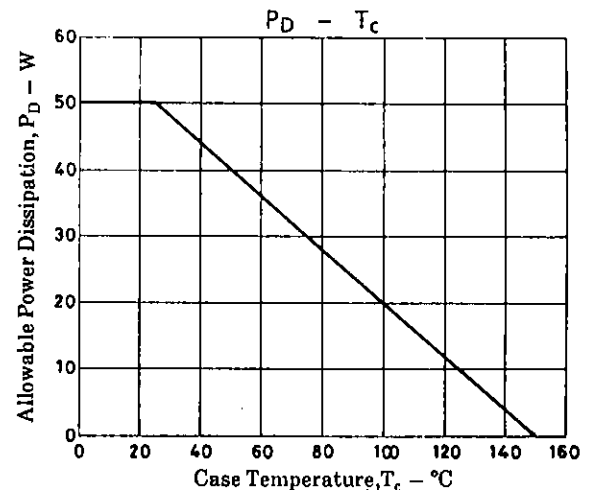
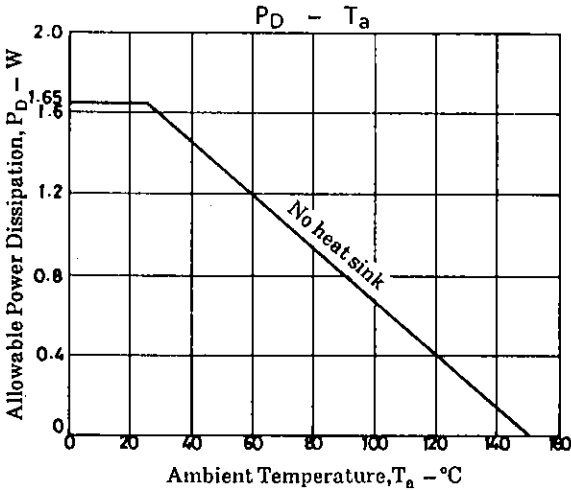
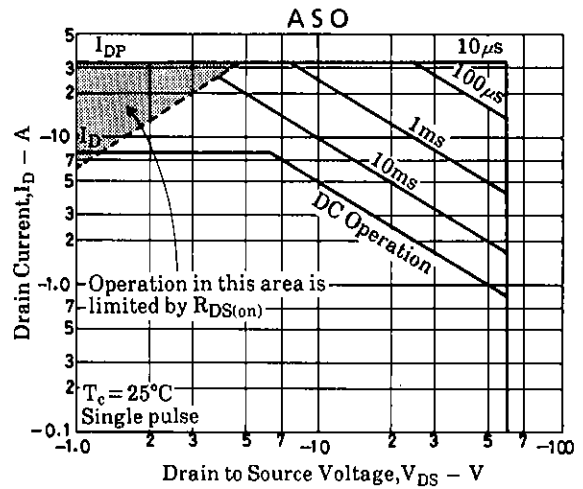
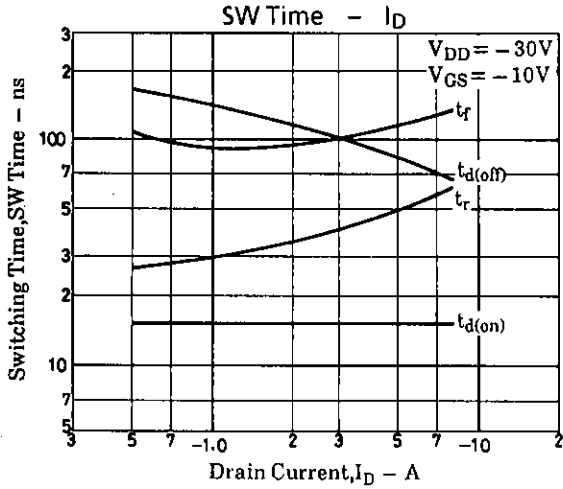
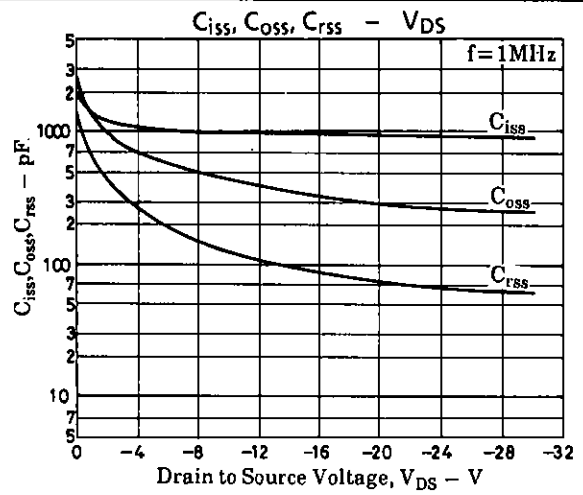
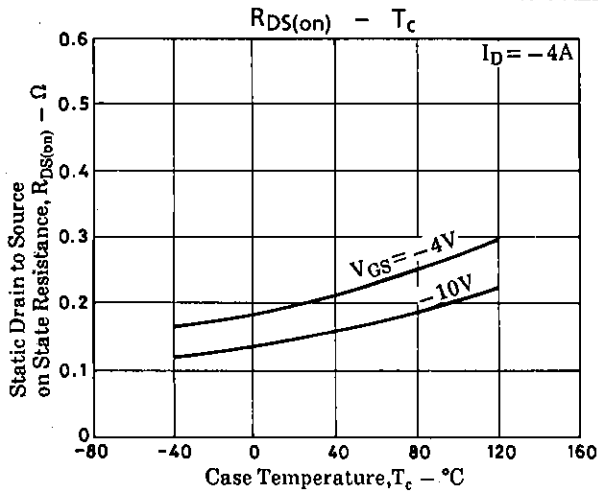
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			min	typ	max	unit
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		950		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		300		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		75		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		15		ns
Rise Time	t_r	"		45		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		90		ns
Fall Time	t_f	"		110		ns
Diode Forward Voltage	V_{SD}	$I_S = -8A, V_{GS} = 0$	-1.0	-1.5		V

Switching Time Test Circuit





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